

## Area1 International Symposium on Nitride Semiconductors (CIRFE Symposium)

11/5	10:15	10:45	Invited	Tomoyosh	Mishima	High Breakdown Voltage Vertical-Structure GaN p-n Junction Diodes
	10:45	11:00	1218	Shun	Lu	Reduction of Specific Contact Resistance on p-type GaN by Thermal Annealed Mg Layer
	11:00	11:15	1026	Naoki	Inoue	First-principles Calculations between Screw Dislocation with Mg, H Impurities on GaN
	11:15	11:30	1176	Susumu	Sasaki	Direct Observation of Spontaneous Polarization in Freestanding GaN Substrate
	11:30	11:45	1080	Akihiro	Shimada	Operando Measurement of Local Piezoelectric Lattice Strain in AlGaN/GaN HEMT Devices by Synchrotron
	11:45	12:00	1115	Takuma	Doi	Schottky barrier height lowering for metal/n-type 4H-SiC contacts using low work function metals
	15:00	15:30	Invited	Yutaka	Mikawa	Acidic Ammonothermal Growth of Bulk GaN
	15:30	15:45	1003	Markus	Pristovsek	AIPN on GaN: A new member of the III-Nitride family
	15:45	16:00	1133	Hiroki	Shimizu	High fracture toughness aluminum nitride (AlN) by AlN-whiskers addition and tape-cast
	16:00	16:15	1143	Zheng	Ye	Comparative Analysis of Decomposition of TMGa and TEGa for the Clarification of the Mechanism of Unintentional Carbon Incorporation in GaN MOVPE
	16:30	17:00	Invited	Filip	Tuomisto	Analyzing the electrical activity of cation and nitrogen vacancies in AlGaN and AlGaN/GaN interfaces
	17:00	17:15	1082	Kieu My	Bui	A Computational Approach of Epitaxial Growth of Gallium Nitride
	17:15	17:30	1163	Toru	Akiyama	Direct approach for calculating individual energy of step edges on polar AlN(0001) and GaN(0001) surfaces using density functional calculations
	17:30	17:45	1160	Akira	Kusaba	Tuning of Reaction Rate Constants for Trimethylgallium Decomposition by Multiobjective Genetic Algorithm with High-Resolution Mass Spectrometry Data
	17:45	18:00	1159	Yoshihiro	Kangawa	Theoretical approach to unintentional oxygen doping during MOVPE of GaN:Mg and AlN:Mg
11/6	9:00	10:00	Plenary	Chris G.	Van de Walle	Exploring (and exploiting) the physics of ultra-wide-bandgap nitrides
	10:00	11:00	Plenary	Tomás	Palacios	New Semiconductor Materials: The Critical Infrastructure to Build the Future
	11:15	11:30	1215	Masahiro	Horita	Investigation of Electron Traps in Homoepitaxial n-type GaN Grown by MOVPE
	11:30	11:45	1190	Meguru	Endo	Nitrogen-displacement-related Hole Traps in N-type GaN with Electron Beam Irradiations in the Energy Range from 100 to 400 keV
	11:45	12:00	1210	Kensuke	Sumida	Isothermal Annealing Study on Mg-implanted Homoepitaxial GaN
	12:00	12:15	1107	Ryosuke	Sakurai	First Principles Studies on Atomic and Electronic Structures of VGa-VN divacancies.

11/6	13:30	14:00	Inited	Masayoshi Yamamoto		SiC/GaN Hybrid Soft Switching Inverter for Electric Vehicle Applications
	14:00	14:30	Inited	Kazuhiro Umetani		Parasitic Inductance Design for High-Power Gallium Nitride Field-Effect Transistors
	14:30	14:45	1058	Sihoon Choi		Feasibility Analysis of Designing Coupled Inductors Using Powder Core in Multiphase Converter
	14:45	15:00	1189	Daisuke Arai		The Switching Characteristics of Cascode Connected GaN-PSJ-FET
	15:15	15:45	Inited	Satoshi Kamiyama		Room-temperature operation of nitride-based multi-quantum shell (MQS)/nanowire lasers
	15:45	16:15	Invied	Åsa Haglund		Membrane-Based Light-emitters from the Blue to the Ultraviolet Wavelength Regime by Electrochemical Etching
	16:15	16:30	1028	Kengo Nagata		Electrochemical Etching
	16:30	16:45	1061	Taichi Matsubara		Sputtered polycrystalline MgZnO as transparent electrode in AlGaN-based  homojunction tunnel junction deep
	16:45	17:00	1209	Pietro Pampili		Nitrogen-polar GaN and AlN templates for light detection application

**11/5 13:30 14:30 Poster**

1173	Keito Aoshima		Hole traps formed by gamma-ray irradiation in homoepitaxial p-type GaN
1180	Takuya Nakashima		Time evolution of crystallographic defects in Mg ion-implanted GaN during annealing
1213	Wentao Cai		High In-content InGaN Platelet as Underlayer for Light-Emitting Diodes toward Long Wavelength Application
1152	Toshiki Achiwa		Investigation of High Frequency and High Voltage Inverter with GaN-HEMT/SiC-JFET Cascode Device
1188	Haruki Hirasawa		"A Study of UV-LEDs Driving Curcuit Including Degration Detection of UV-LEDs and Curcuit"